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 Roll No.
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# B. TECH (SEM-VII) THEORY EXAMINATION 2018-19 VLSI DESIGN

Time: 3 Hours Total Marks: 100

**Note: 1.** Attempt all Sections. If require any missing data; then choose suitably.

#### SECTION A

## 1. Attempt all questions in brief.

 $2 \times 10 = 20$ 

- a. Why we need a low power VLSI circuits in today's scenario?
- b. Explain the terms packaging and testing.
- c. Define logical effort with example.
- d. Define the terms- Defects, Errors and Faults.
- e. Distinguish between SRAM and DRAM.
- f. Bring out the drawbacks of dynamic logic.
- g. Explain the term controllability and observability.
- h. Why we prefer CMOS transmission gates over other gates?
- i. Define the term Interconnect.
- j. What is meant by Stuck-at-1(s-a-1) fault and Stuck-at-0(s-a-0) faults.

## SECTION B

# 2. Attempt any three of the following:

10 x 3 ≠ 30

- a. Illuminate the n-well CMOS fabrication process with neat diagrams,
- b. Explain the Elmore Delay Model with suitable diagram.
- c. Write short note on:
  - (i) Logical Effort
  - (ii) Parasitic Delay
- d. Enlist the advantages of dynamic logic circuit over static logic circuit. Explain NORA CMOS logic circuit with suitable example.
- e. Describe leakage power dissipation and dynamic power dissipation.

### SECTION C

# 3. Attempt any one part of the following:

 $10 \times 1 = 10$ 

- (a) (i) Write short note on VLSI testing.
  - (ii) Draw and explain the VLSI design Flow(Y-chart).
- (b) Draw and explain the working of CMOS inverter with its transfer characteristics.

## 4. Attempt any one part of the following:

 $10 \times 1 = 10$ 

- (a) Analyze the Linear delay model with its different limitations.
- (b) Explain the following circuits:
  - (i) Variable threshold CMOS circuits
  - (ii) Multiple threshold CMOS circuits

## 5. Attempt any one part of the following:

 $10 \times 1 = 10$ 

- (a) Draw and explain the working of Lumped RC-model for interconnects.
- (b) Explain the Delay Estimation with different optimization techniques.

# 6. Attempt any one part of the following:

 $10 \times 1 = 10$ 

- (a) Explain read/write operation of SRAM memory cell. How 1-bit cell is used in bigger memory systems.
- (b) (i) Implement the Boolean function Y = AB + (C+D)(F+E)+GH using DOMINO CMOS logic.
  - (ii) Explain the term Voltage Boot Strapping in CMOS logic with suitable examples.

# 7. Attempt any *one* part of the following:

 $10 \times 1 = 10$ 

- (a) Explain the issues involved in Built-in Self Test (BIST) techniques in detail.
- (b) (i) Write a short note on Adiabatic Logic Circuit.
  - (ii) Explain the Scan Based Techniques.